MO2018

High Temp, Single-Chip, SOT23 Oscillator



Features

- Frequencies between 1 MHz and 110 MHz accurate to 6 decimal places
- Operating temperature from -40°C to +125°C. For -55°C option, refer to MO2020 and MO2021
- Supply voltage of +1.8V or +2.5V to +3.3V
- Excellent total frequency stability as low as ±20ppm
- Low power consumption of +3.5mA typical at 20 MHz, +1.8V
- LVCMOS/LVTTL compatible output
- 5-pin SOT23-5 package: 2.9mm x 2.8mm
- RoHS and REACH compliant, Pb-free, Halogen-free and Antimony-free
- For AEC-Q100 clock generators, refer to MO2024 and MO2025

Applications

- Industrial, medical, automotive, avionics and other high temperature applications
- Industrial sensors, PLC, motor servo, outdoor networking equipment, medical video cam, asset tracking systems, etc.





Ph-Free

RoHS Compliant

Electrical Specifications

Table 1. Electrical Characteristics

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at +25°C and nominal supply voltage.

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition		
			F	requency R	ange			
Output Frequency Range	f	1.0	-	110	MHz	Refer to Table 14 for the exact list of supported frequencies list of supported frequencies		
			Frequer	ncy Stability	and Aging	l		
		-20	_	+20	ppm			
F	F -4-b	-25	_	+25	ppm	Inclusive of Initial tolerance at +25°C, 1st year aging at +25°C,		
Frequency Stability	F_stab	-30	-	+30	ppm	and variations over operating temperature, rated power supply voltage and load (15 pF ±10%).		
		-50	-	+50	ppm			
			Operati	ng Tempera	ture Range	•		
Operating Temperature Range	T 1100	-40	-	+105	°C	Extended Industrial		
(ambient)	T_use	-40	-	+125	°C	Automotive		
		Sı	upply Voltag	e and Curre	ent Consun	nption		
		+1.62	+1.8	+1.98	V			
		+2.25	+2.5	+2.75	V			
Supply Voltage	Vdd	+2.52	+2.8	+3.08	V			
Supply Voltage		+2.7	+3.0	+3.3	V			
		+2.97	+3.3	+3.63	V			
		+2.25	-	+3.63	V			
		-	+3.8	+4.7	mA	No load condition, $f = 20$ MHz, $Vdd = +2.8V$, $+3.0V$ or $+3.3V$		
Current Consumption	ldd	-	+3.6	+4.5	mA	No load condition, f = 20 MHz, Vdd = +2.5V		
			+3.5	+4.5	mA	No load condition, f = 20 MHz, Vdd = +1.8V		
OE Disable Current	I od	-	_	+4.5	mA	Vdd = +2.5V to $+3.3V$, $OE = Low$, Output in high Z state.		
OL Disable Current	1_00	-	_	+4.3	mA	Vdd = +1.8V, OE = Low, Output in high Zstate.		
		-	+2.6	+8.5	μA	Vdd = +2.8V to +3.3V, ST = Low, Output is weakly pulled down		
Standby Current	I_std	-	+1.4	+5.5	μA	Vdd = +2.5V, ST = Low, Output is weakly pulled down		
			+0.6	+4.0	μA	Vdd = +1.8V, ST = Low, Output is weakly pulled down		
			LVCMOS	OutputCha	aracteristic	s		
Duty Cycle	DC	45	-	55	%	All Vdds		
		-	1.0	2.0	ns	Vdd = +2.5V, +2.8V, +3.0V or +3.3V, 20% - 80%		
Rise/Fall Time	Tr, Tf	ı	1.3	2.5	ns	Vdd =+1.8V, 20% - 80%		
		-	1.0	3.0	ns	Vdd = +2.25V - +3.63V, 20% - 80%		
Output High Voltage	VOH	90%	_	-	Vdd	IOH = -4.0 mA (Vdd = +3.0V or +3.3V) IOH = -3.0 mA (Vdd = +2.8V or +2.5V) IOH = -2.0 mA (Vdd = +1.8V)		
Output Low Voltage	VOL	-	-	10%	Vdd	IOL = +4.0 mA (Vdd = +1.8V) IOL = +4.0 mA (Vdd = +3.0V or +3.3V) IOL = +3.0 mA (Vdd = +2.8V or +2.5V) IOL = +2.0 mA (Vdd = +1.8V)		



Table 1. Electrical Characteristics (continued)

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition			
			Inp	ut Characte	ristics				
Input High Voltage	VIH	70%	-	ı	Vdd	Pin 3, OE or ST			
Input Low Voltage	VIL	-	ı	30%	Vdd	Pin 3, OE or ST			
Input Pull-up Impedence	Z_in	50	87	150	kΩ	Pin 3, OE logic high or logic low, or ST logic high			
input Fun-up impedence	2_111	2.0	-	-	МΩ	Pin 3, ST logic low			
	Startup and Resume Timing								
Startup Time	T_start	-	-	5.0	ms	Measured from the time Vdd reaches its rated minimum value			
Enable/Disable Time	T_oe	-	-	130	ns	f = 110 MHz. For other frequencies, T_oe = 100 ns + 3 * clock periods			
Resume Time	T_resume	-	-	5.0	ms	Measured from the time ST pin crosses 50%threshold			
				Jitter					
DMC Davied litter	Т ::++	-	1.6	2.5	ps	f = 75 MHz, Vdd = +2.5V, +2.8V, +3.0V or +3.3V			
RMS Period Jitter	T_jitt	-	1.9	3.0	ps	f = 75 MHz, Vdd = +1.8V			
Paris to mark Paris d 1944	T ale	-	12	20	ps	f = 75 MHz, Vdd = +2.5V, +2.8V, +3.0V or +3.3V			
Peak-to-peak Period Jitter	T_pk	-	14	25	ps	f = 75 MHz, Vdd = +1.8V			
DMC Dhoos litter/rende	Tinhi	-	0.5	0.8	ps	f = 75 MHz, Integration bandwidth = 900 kHz to 7.5 MHz			
RMS Phase Jitter (random)	T_phj	-	1.3	2.0	ps	f = 75 MHz, Integration bandwidth = 12 kHz to 20 MHz			

Table 2. Pin Description

Pin	Symbol		Functionality
1	GND	Power	Electrical ground
2	NC	No Connect	No connect
		Output Enable	H ^[1] : specified frequency output L: output is high impedance. Only output driver is disabled.
3	3 OE/ST/NC	Standby	H or Open ^[1] : specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Supply current reduces to I_std.
	No C		Any voltage between 0 and Vdd or Open ^[1] : Specified frequency output. Pin 3 has no function.
4	VDD	Power	Power supply voltage ^[2]
5	OUT	Output	Oscillator output

Notes:

- 1. In OE or \overline{ST} mode, a pull-up resistor of 10 k Ω or less is recommended if pin 3 is not externally driven. If pin 3 needs to be left floating, use the NC option.
- 2. A capacitor of value 0.1 μF or higher between Vdd and GND is required.

Top View

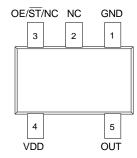


Figure 1. Pin Assignments

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Table 3. Absolute Maximum Limits

Attempted operation outside the absolute maximum ratings of the part may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	+150	°C
Vdd	-0.5	+4.0	V
Electrostatic Discharge	-	+2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	-	+260	°C
Junction Temperature ^[3]	-	+150	°C

Noto:

Table 4. Thermal Consideration^[4]

Package	θ _{JA} , 4 Layer Board (°C/W)	θ _{JC} , Bottom (°C/W)
SOT23-5	421	175

Note:

4. Refer to JESD51 for θ_{JA} and θ_{JC} definitions, and reference layout used to determine the θ_{JA} and θ_{JC} values in the above table.

Table 5. Maximum Operating Junction Temperature^[5]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
+105°C	+115°C
+125°C	+135°C

Note

5. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 6. Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method2002
Mechanical Vibration	MIL-STD-883F, Method2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method2003
Moisture Sensitivity Level	MSL1 @ 260°C

^{3.} Exceeding this temperature for extended period of time may damage the device.



Test Circuit and Waveform^[6]

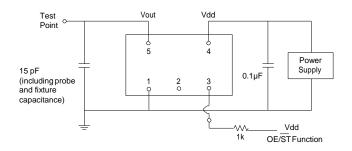


Figure 2. Test Circuit

Note:

6. Duty Cycle is computed as Duty Cycle =TH/Period.

Tr — Tf 80% Vdd 50% 20% Vdd High Pulse (TH) Period Period

Figure 3. Output Waveform

Timing Diagrams

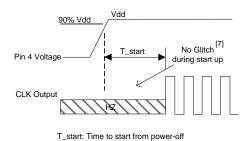
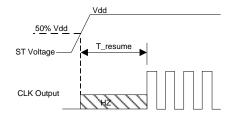
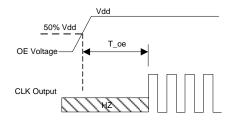


Figure 4. Startup Timing (OE/ST Mode)

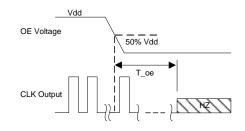


T_resume: Time to resume from ST

Figure 5. Standby Resume Timing (ST Mode Only)



T_oe: Time to re-enable the clock output



T_oe: Time to put the output in High Z mode

Figure 6. OE Enable Timing (OE Mode Only)

Note:

7. MO2018 has "no runt" pulses and "no glitch" output during startup or resume.

Figure 7. OE Disable Timing (OE Mode Only)



Performance Plots^[8]

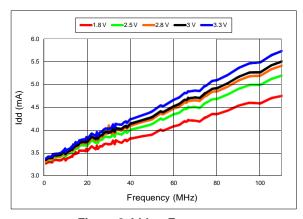


Figure 8. Idd vs Frequency

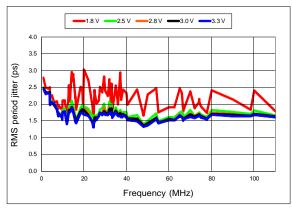


Figure 10. RMS Period Jitter vs Frequency

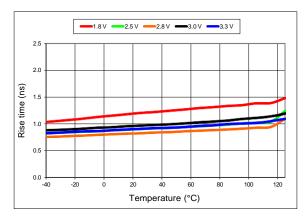


Figure 12. 20%-80% Rise Timevs Temperature

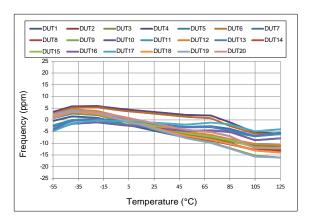


Figure 9. Frequency vs Temperature

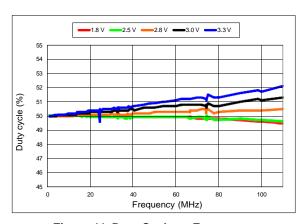


Figure 11. Duty Cycle vs Frequency

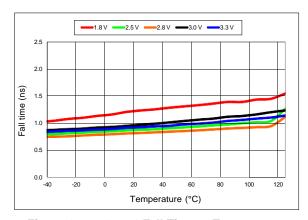
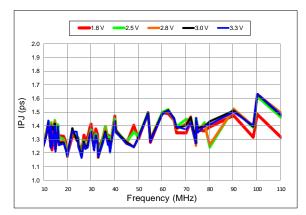


Figure 13. 20%-80% Fall Time vs Temperature



Performance Plots^[8]



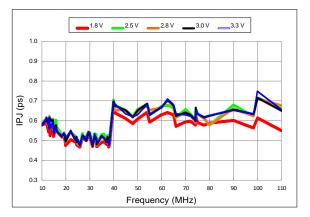


Figure 14. RMS Integrated Phase Jitter Random (12k to 20 MHz) vs Frequency^[9]

Figure 15. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency^[9]

Notes:

- 8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
- 9. Phase noise plots are measured with Agilent E5052B signal source analyzer. Integration range is up to 5 MHz for carrier frequencies up to 40 MHz.



Programmable Drive Strength

The MO2018 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, contact KDS.

EMI Reduction by Slowing Rise/Fall Time

Figure 16 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

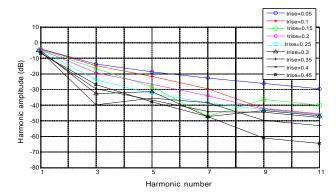


Figure 16. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to speed up the rise/fall time of the input clock. Some chipsets may also require faster rise/fall time in order to reduce their sensitivity to this type of jitter. Refer to the Rise/Fall Time Tables (Table 7 to Table 11) to determine the proper drive strength.

High Output Load Capability

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a +3.3V MO2018 device with default drive strength setting, the typical rise/fall time is 1ns for 15 pF output load. The typical rise/fall time slows down to 2.6 ns when the output load increases to 45 pF. One can choose to speed up the rise/fall time to 1.83 ns by then increasing the drive strength setting on the MO2018.

The MO2018 can support up to 60 pF in maximum capacitive loads with drive strength settings. Refer to the Rise/Tall Time Tables (Table 7 to 11) to determine the proper drive strength for the desired combination of output load vs. rise/fall time

MO2018 Drive Strength Selection

Tables 7 through 11 define the rise/fall time for a given capacitive load and supply voltage.

- 1. Select the table that matches the MO2018 nominal supply voltage (+1.8V, +2.5V, +2.8V, +3.0V, +3.3V).
- Select the capacitive load column that matches the application requirement (5 pF to 60 pF)
- Under the capacitive load column, select the desired rise/fall times.
- 4. The left-most column represents the part number code for the corresponding drive strength.
- Add the drive strength code to the part number for ordering purposes.

Calculating Maximum Frequency

Based on the rise and fall time data given in Tables 7 through 11, the maximum frequency the oscillator can operate with guaranteed full swing of the output voltage over temperature can be calculated as the following:

Max F requency =
$$\frac{1}{5 \times T \text{ rf}_2 0/80}$$

where Trf_20/80 is the typical value for 20%-80% rise/fall time.

Example 1

Calculate f_{MAX} for the following condition:

- Vdd = +1.8V (Table 7)
- · Capacitive Load: 30 pF
- Desired Tr/f time = 3 ns (rise/fall time part number code = E)

Part number for the above example:

MO2018EE5-CEH-18E0-0025000025



Drive strength code is here.



Rise/Fall Time (20% to 80%) vs C_{LOAD} Tables

Table 7. Vdd = +1.8V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)							
Drive Strength \C _{LOAD}	5 pF 15 pF 30 pF 45 pF 60 pF						
L	6.16	11.61	22.00	31.27	39.91		
Α	3.19	6.35	11.00	16.01	21.52		
R	2.11	4.31	7.65	10.77	14.47		
В	1.65	3.23	5.79	8.18	11.08		
T	0.93	1.91	3.32	4.66	6.48		
E	0.78	1.66	2.94	4.09	5.74		
U	0.70	1.48	2.64	3.68	5.09		
F or "0": default	0.65	1.30	2.40	3.35	4.56		

Table 9. Vdd = +2.8V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)							
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF	45 pF	60 pF		
L	3.77	7.54	12.28	19.57	25.27		
Α	1.94	3.90	7.03	10.24	13.34		
R	1.29	2.57	4.72	7.01	9.06		
В	0.97	2.00	3.54	5.43	6.93		
T	0.55	1.12	2.08	3.22	4.08		
E or "0": default	0.44	1.00	1.83	2.82	3.67		
U	0.34	0.88	1.64	2.52	3.30		
F	0.29	0.81	1.48	2.29	2.99		

Table 11. Vdd = +3.3V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)								
Drive Strength \ C _{LOAD}	ive Strength \ C _{LOAD} 5 pF 15 pF 30 pF 45 pF 60 pF							
L	3.39	6.88	11.63	17.56	23.59			
Α	1.74	3.50	6.38	8.98	12.19			
R	1.16	2.33	4.29	6.04	8.34			
В	0.81	1.82	3.22	4.52	6.33			
T or "0": default	0.46	1.00	1.86	2.60	3.84			
E	0.33	0.87	1.64	2.30	3.35			
U	0.28	0.79	1.46	2.05	2.93			
F	0.25	0.72	1.31	1.83	2.61			

Table 8. Vdd = +2.5V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)							
Drive Strength \C _{LOAD}	5 pF	15 pF	30 pF	45 pF	60 pF		
L	4.13	8.25	12.82	21.45	27.79		
Α	2.11	4.27	7.64	11.20	14.49		
R	1.45	2.81	5.16	7.65	9.88		
В	1.09	2.20	3.88	5.86	7.57		
T	0.62	1.28	2.27	3.51	4.45		
E or "0": default	0.54	1.00	2.01	3.10	4.01		
U	0.43	0.96	1.81	2.79	3.65		
F	0.34	0.88	1.64	2.54	3.32		

Table 10. Vdd = +3.0V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)								
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF	45 pF	60 pF			
L	3.60	7.21	11.97	18.74	24.30			
Α	1.84	3.71	6.72	9.86	12.68			
R	1.22	2.46	4.54	6.76	8.62			
В	0.89	1.92	3.39	5.20	6.64			
T or "0": default	0.51	1.00	1.97	3.07	3.90			
E	0.38	0.92	1.72	2.71	3.51			
U	0.30	0.83	1.55	2.40	3.13			
F	0.27	0.76	1.39	2.16	2.85			



Pin 3 Configuration Options (OE, ST, or NC)

Pin 3 of the MO2018 can be factory-programmed to support three modes: Output Enable (OE), standby (\overline{ST}) or No Connect (NC).

Output Enable (OE) Mode

In the OE mode, applying logic Low to the OE pin only disables the output driver and puts it in Hi-Z mode. The core of the device continues to operate normally. Power consumption is reduced due to the inactivity of the output. When the OE pin is pulled High, the output is typically enabled in <1µs.

Standby (ST) Mode

In the ST mode, a device enters into the standby mode when Pin 3 pulled Low. All internal circuits of the device are turned off. The current is reduced \underline{to} a standby current, typically in the range of a few μA . When \overline{ST} is pulled High, the device goes through the "resume" process, which can take up to 5 ms.

No Connect (NC) Mode

In the NC mode, the device always operates in its normal mode and outputs the specified frequency regardless of the logic level on pin 3.

Table 12 below summarizes the key relevant parameters in the operation of the device in OE, ST, or NC mode.

Table 12. OE vs. ST vs. NC

	OE	ST	NC
Active current 20 MHz (max, +1.8V)	+4.5 mA	+4.5 mA	+4.5 mA
OE disable current (max. +1.8V)	+4.3 mA	N/A	N/A
Standby current (typical +1.8V)	N/A	+0.6 µA	N/A
OE enable time at 110 MHz (max)	130 ns	N/A	N/A
Resume time from standby (max, all frequency)	N/A	5.0 ms	N/A
Output driver in OE disable/standby mode	High Z	weak pull-down	N/A

Output on Startup and Resume

The MO2018 comes with gated output. Its clock output is accurate to the rated frequency stability within the first pulse from initial device startup or resume from the standby mode.

In addition, the MO2018 supports "no runt" pulses, and "no glitch" output during startup or resume as shown in the waveform captures in Figure 17 and Figure 18.

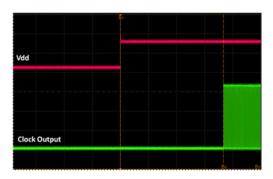


Figure 17. Startup Waveform vs. Vdd

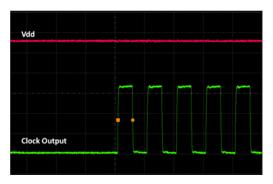
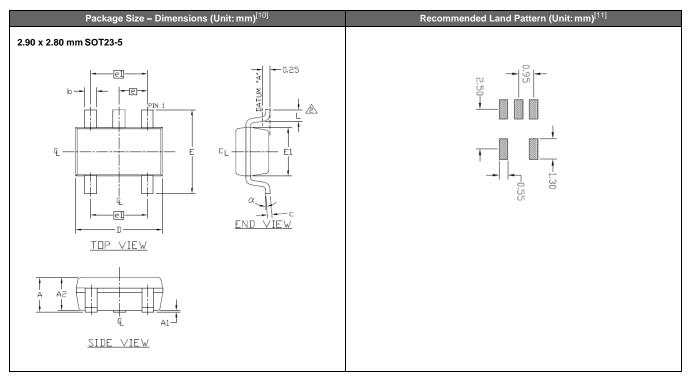


Figure 18. Startup Waveform vs. Vdd (Zoomed-in View of Figure 17)



Dimensions and Patterns



Notes

10. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device. 11. A capacitor value of 0.1 µF between Vdd and GND is required

Table 13. Dimension Table

Symbol	Min.	Nom.	Max.
Α	0.90	1.27	1.45
A1	0.00	0.07	0.15
A2	0.90	1.20	1.30
b	0.30	0.35	0.50
С	0.14	0.15	0.20
D	2.75	2.90	3.05
E	2.60	2.80	3.00
E1	1.45	1.60	1.75
L	0.30	0.38	0.55
L1	0.25 REF		
е	0.95 BSC.		
e1	1.90 BSC.		
α	0°		8°



Ordering Information

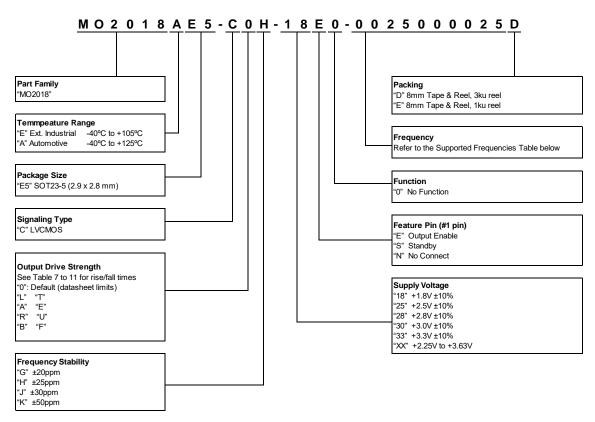


Table 14. List of Supported Frequencies^[12, 13]

Frequency Range (-40 to +105°C or -40 to +125°C)			
Min.	Max.		
1.000000 MHz	61.222999 MHz		
61.674001 MHz	69.795999 MHz		
70.485001 MHz	79.062999 MHz		
79.162001 MHz	81.427999 MHz		
82.232001 MHz	91.833999 MHz		
92.155001 MHz	94.248999 MHz		
94.430001 MHz	94.874999 MHz		
94.994001 MHz	97.713999 MHz		
98.679001 MHz	110.000000 MHz		

Notes:

- 12. Any frequency within the min and max values in the above table are supported with 6 decimal places of accuracy.
- 13. Please contact KDS for frequencies that are not listed in the tables above.

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Revision History

Table 15. Datasheet Version and Change Log

Version	Release Date	Change Summary
1.0	05/14/2015	Final Production Release.
1.01	09/29/2015	Revised the dimension table
1.02	04/27/2015	Changed Clock Generator to SOT23 Oscillator